**Product data sheet** 

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT186A "full pack" plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching. This sensitive gate "series E" triac is intended for gate triggering by low power drivers and microcontrollers.

### 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- · High blocking voltage capability
- Isolated package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- · Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{DRM}$	repetitive peak off-state voltage			6	000		V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 38$ °C; Fig. 1; Fig. 2; Fig. 3	16		А		
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	155			А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-;}$ $T_j = 25 \text{ °C; Fig. 7}$		-	4	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	11	25	mA

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		N
3	G	gate		T2 T1
mb	n.c.	mounting base; isolated		sym051

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	number Package					
	Name	Description	Version			
BT139X-600E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BT139X-600E	BT139X-600E

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

repetitive peak off-state			
voltage		600	V
RMS on-state current	full sine wave; $T_h \le 38 ^{\circ}\text{C}$ ; Fig 1; Fig 2; Fig 3	16	А
non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig 4; Fig 5	155	Α
	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	170	Α
I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	120	A <sup>2</sup> s
rate of rise of on-state current	I <sub>G</sub> = 20 mA; T2+ G+	50	A/µs
	I <sub>G</sub> = 20 mA; T2+ G-	50	A/µs
	I <sub>G</sub> = 20 mA; T2- G-	50	A/µs
	I <sub>G</sub> = 50 mA; T2- G+	10	A/µs
peak gate current		2	А
peak gate power		5	W
average gate power	over any 20 ms period	0.5	W
storage temperature		-40 to 150	°C
junction temperature		125	°C
	RMS on-state current  non-repetitive peak on- state current  I²t for fusing rate of rise of on-state current  peak gate current  peak gate power average gate power storage temperature	RMS on-state current	RMS on-state current

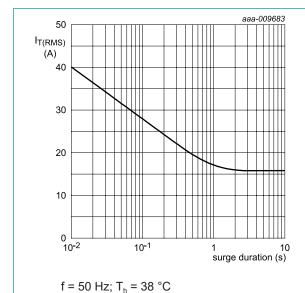


Fig. 1. RMS on-state current as a function of surge duration; maximum values

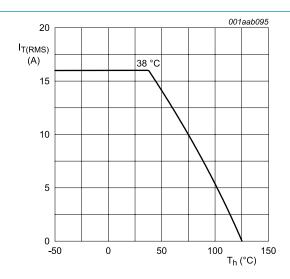
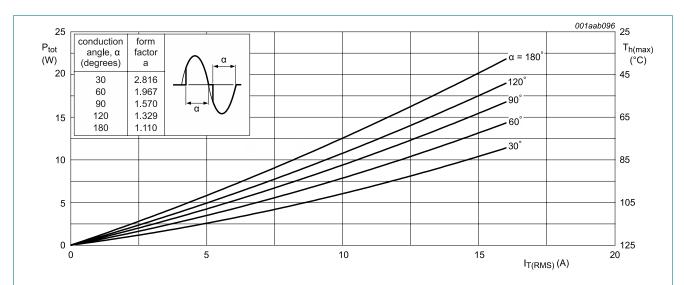


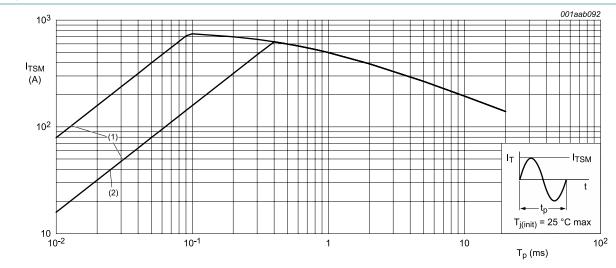
Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms}$ 

- $(1) dI_{T}/dt limit$
- (2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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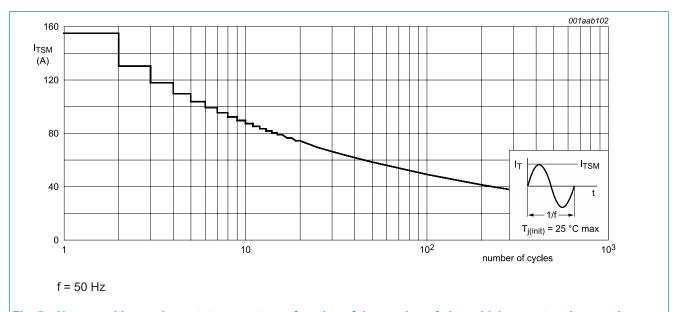
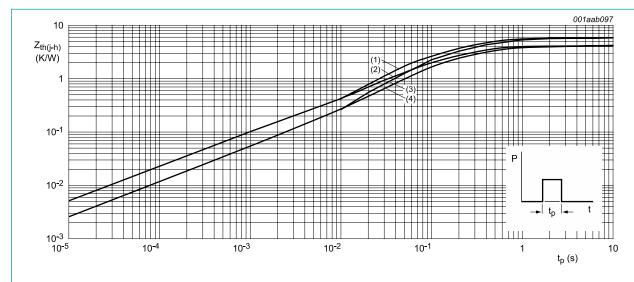


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig 6	-	-	4	K/W
	heatsink	full or half cycle; without heatsink compound; Fig 6	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

### 10. Isolation characteristics

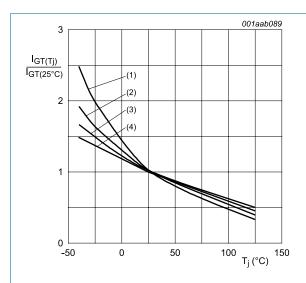
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; $T_h = 25$ °C	-	-	2500	٧
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

### 11. Characteristics

#### **Table 8. Characteristics**

<b>Symbol</b>	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	25	mA
l <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	3.2	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	4	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	5.5	40	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	4	30	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					-
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	50	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$V_D = 600 \text{ V}; I_{TM} = 20 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

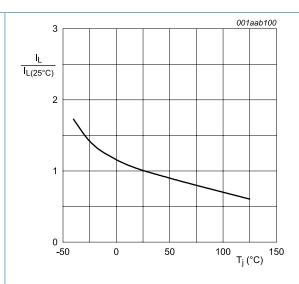


Fig. 8. Normalized latching current as a function of junction temperature

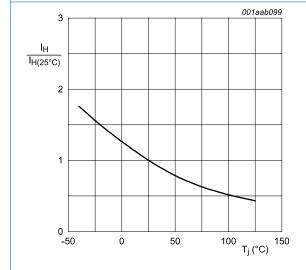
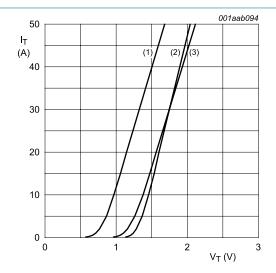


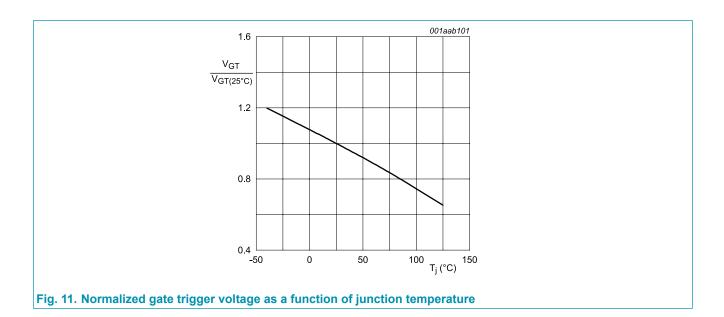
Fig. 9. Normalized holding current as a function of junction temperature



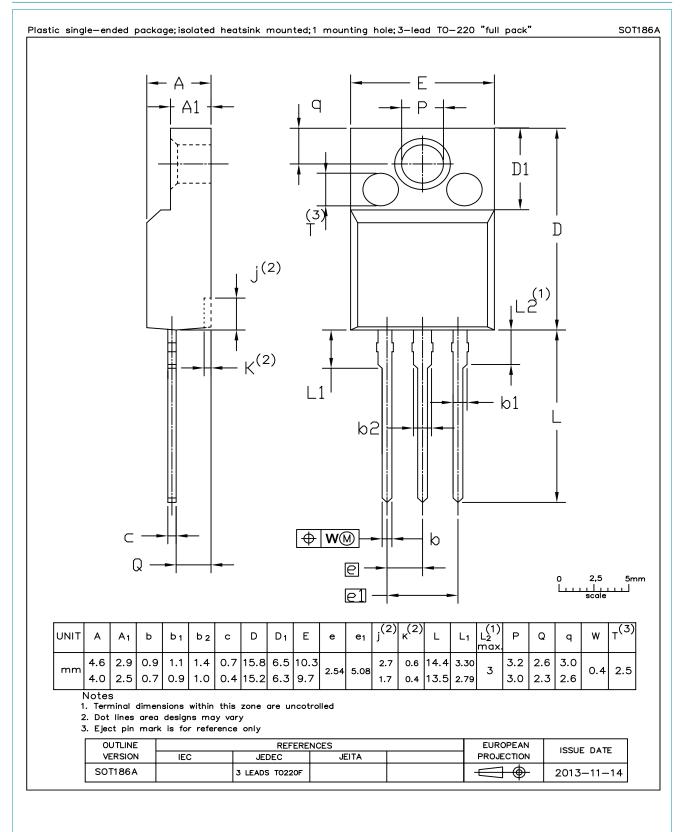
 $V_o$  = 1.195 V;  $R_s$  = 0.018 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



## 12. Package outline



### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com
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